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NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI HF100-28** is a class A silicon NPN planar transistor, designed for SSB communications. Diffused ballasting provide High VSRW Capability under rated operating conditions.

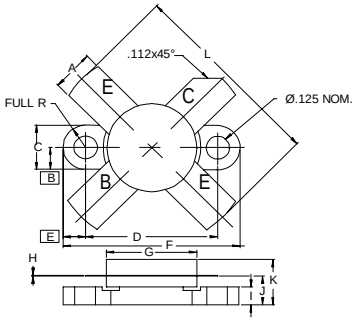
FEATURES:

- P_G = 15 dB min. at 100 W/30 MHz
- High linear power output
- IMD_3 = -30 dBc max. at 100 W(PEP)
- ***Omnigold***™ Metalization System
- 28 V CE operation

MAXIMUM RATINGS

I_C	20 A
V_{CBO}	65 V
V_{CEO}	36 V
V_{EBO}	4.0 V
P_{DISS}	270 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.65 °C/W

PACKAGE STYLE .500 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.7.30 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K		.280 / 7.11
L	.980 / 24.89	1.050 / 26.67

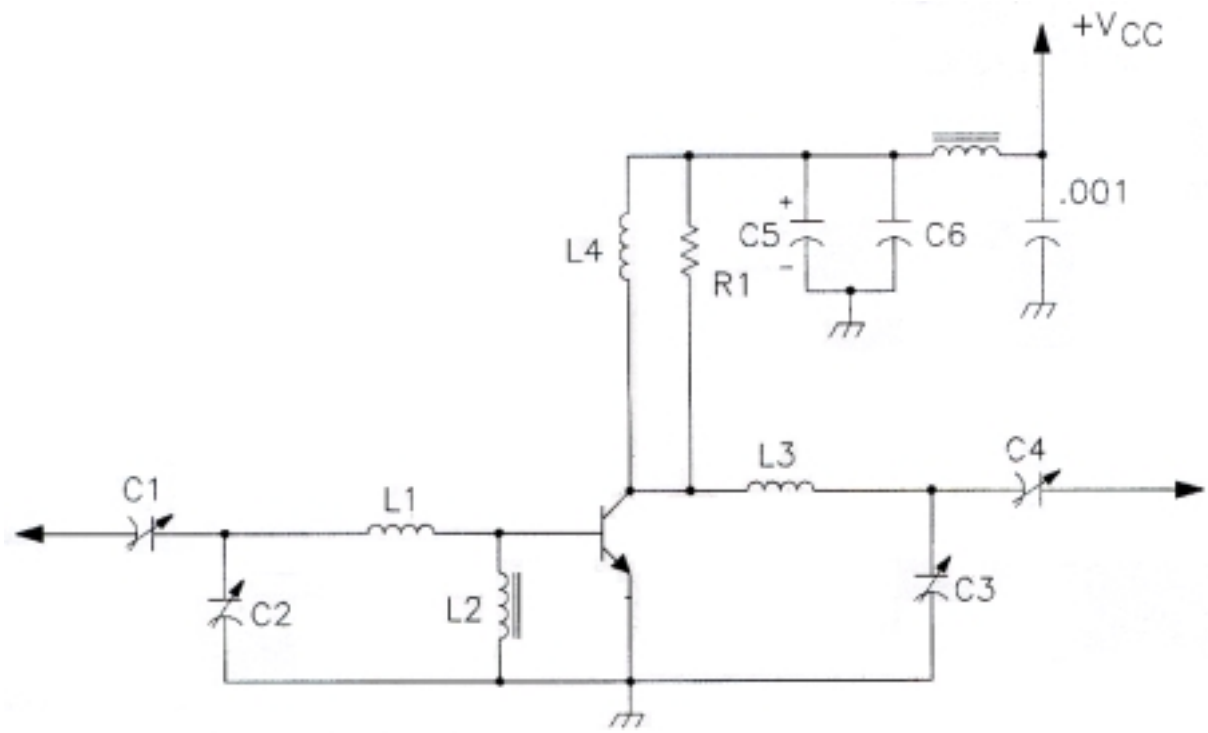
ORDER CODE: ASI10608

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 100 mA	35			V
BV_{CES}	I_C = 100 mA	65			V
BV_{CBO}	I_C = 100 mA	65			
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CES}	V_{CE} = 30 V			15	mA
h_{FE}	V_{CE} = 5.0 V I_C = 5.0 A	10		200	---
C_{ob}	V_{CB} = 30 V f = 1.0 MHz	---		285	pF
G_P	V_{CE} = 28 V P_{IN} = 3.16 W P_{PUT} = 100 W	15	16		dB
IMD_3	f_1 = 30.000 MHz I_{CQ} = 100 mA f_2 = 30.001 MHz		-34	-30	dBc

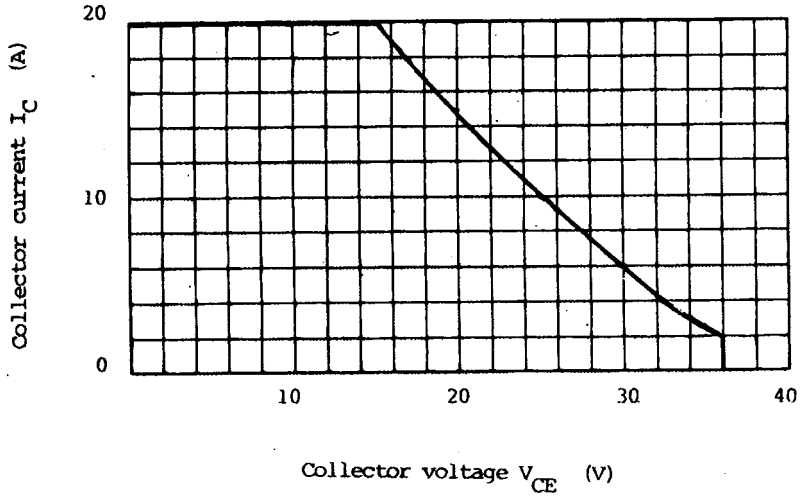
Specifications are subject to change without notice.

TEST CIRCUIT



C1	:	24 - 200pF Arco 425	L1	:	4 Turns, #16 AWG, Tinned, 0.40" I.D.
C2,C4	:	50 - 380pF Arco 465	L2,L5	:	1 Turn, #22 AWG, Tinned, formed with VK-200 #4B Ferroxcube
C3	:	9 - 180pF Arco 463			
C5	:	10µF, Electrolytic, 35Vdc	L4	:	17 Turns, #18 Enameled Wire Wrapped Around R1
C6	:	0.01µF, 100V, Ceramic	R1	:	390Ω Resistor (2 Watt)

SAFE OPERATING AREA



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